



DMN3025LFG

### 30V N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI<sup>®</sup>

### **Product Summary**

V <sub>(BR)DSS</sub>	RDS(ON) Max	I <sub>D Max</sub> T <sub>A</sub> = +25°C	
30V	18mΩ @ V <sub>GS</sub> = 10V	7.5A	
300	28mΩ @ V <sub>GS</sub> = 4.5V	6.1A	

# Description

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

### Features

- Low R<sub>DS(ON)</sub> ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% Unclamped Inductive Switch (UIS) test in production
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

# **Mechanical Data**

- Case: POWERDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 <sup>®</sup>3

Top View

Internal Schematic

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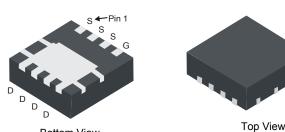
• Weight: 0.072 grams (approximate)

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POWERDI3333-8

Bottom View

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3025LFG-7	POWERDI3333-8	2000/Tape & Reel
DMN3025LFG-13	POWERDI3333-8	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and</li>

<1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**



N25 = Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year (ex: 11 = 2011) WW = Week code (01 ~ 53)



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	Ι <sub>D</sub>	7.5 6.1	A
	t<10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	Ι <sub>D</sub>	10 7.8	A
Maximum Continuous Body Diode Forward Current (Note 5)			ls	2.5	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	60	А
Avalanche Current (Note 6) L = 0.1mH			I <sub>AR</sub>	14	А
Avalanche Energy (Note 6) L = 0.1mH			E <sub>AR</sub>	10	mJ

# **Thermal Characteristics**

Characteristic	Symbol	Value	Units		
Tatal Bower Dissinction (Note 5)	T <sub>A</sub> = +25°C	C	2.0	w	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	PD	1.3		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	61		
mermai Resistance, Junction to Ambient (Note 5)	t < 10s	$R_{ heta JA}$	37	°C/W	
Thermal Resistance, Junction to Case	$R_{ ext{ heta}JC}$	6.4			
Operating and Storage Temperature Range		TJ, TSTG	-55 to 150	°C	

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

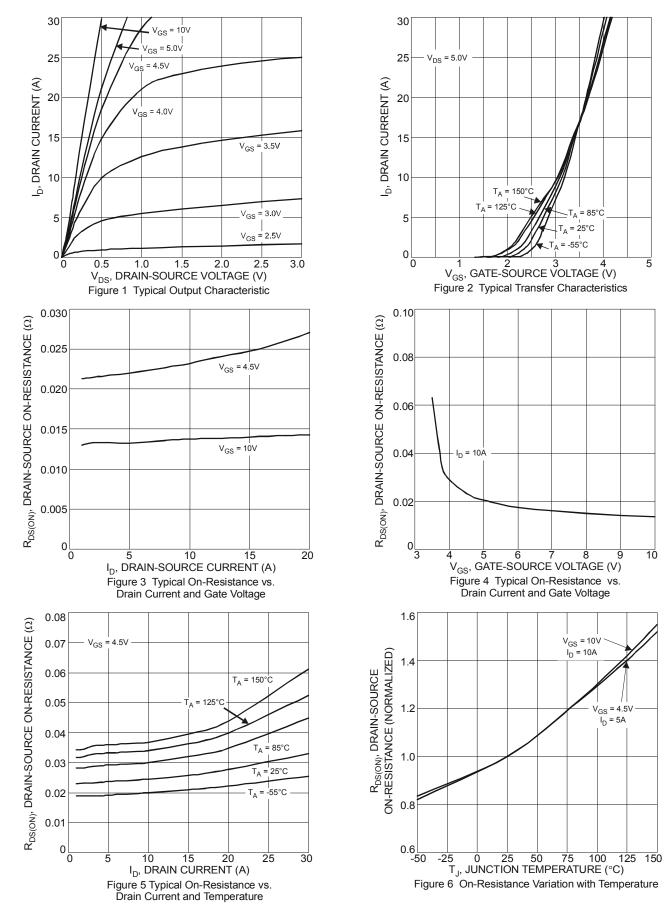
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			i	i	·	1	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	—	1	μA	$V_{DS}$ = 30V, $V_{GS}$ = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±1	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.8	-	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	D		14	18	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 7.8A	
	R <sub>DS (ON)</sub>		23	28	111.5.2	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7.0A	
Forward Transfer Admittance	Y <sub>fs</sub>		9	-	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 7.8A	
Diode Forward Voltage	V <sub>SD</sub>		0.70	1.0	V	$V_{GS} = 0V, I_{S} = 6.3A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		605	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	74	_			
Reverse Transfer Capacitance	C <sub>rss</sub>	_	58	_			
Gate resistance	Rg		1.5	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg		5.3	—		V <sub>DS</sub> = 15V, I <sub>D</sub> = 7.8A	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	11.6	—	nC		
Gate-Source Charge	Qgs		2	—	110		
Gate-Drain Charge	Q <sub>gd</sub>	_	2.4	—			
Turn-On Delay Time	t <sub>D(on)</sub>		3.8	_		V <sub>DD</sub> = 15V, V <sub>GS</sub> = 4.5V, R <sub>L</sub> = 2.4Ω, R <sub>G</sub> = 1Ω,	
Turn-On Rise Time	tr		4.1	_	20		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	17.9	_	ns		
Turn-Off Fall Time	tf	_	4.7	—	]		
Reverse Recovery Time	t <sub>rr</sub>	_	5.5		ns	1 - 120 di/dt - 5000///10	
Reverse Recovery Charge	Qrr	_	2.6	_	nC	I <sub>F</sub> = 12A, di/dt = 500A/μs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. 6.  $I_{AR}$  and  $E_{AR}$  rating are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing. Notes:

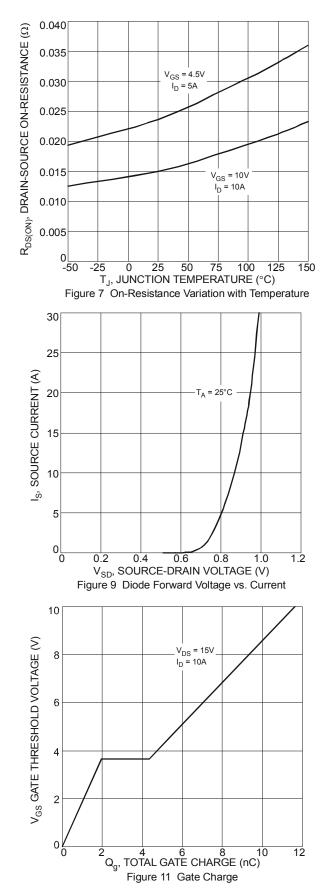


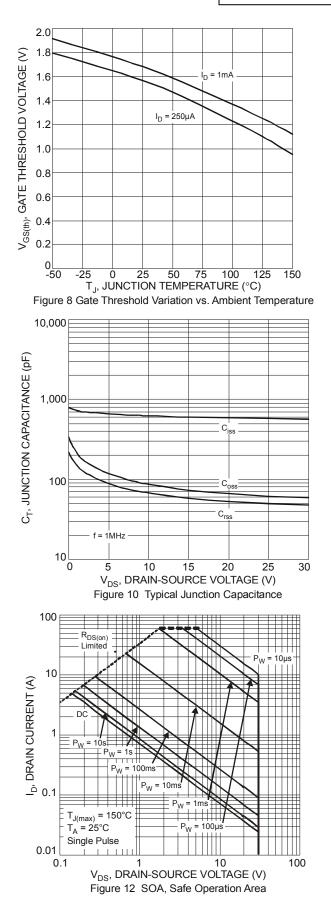
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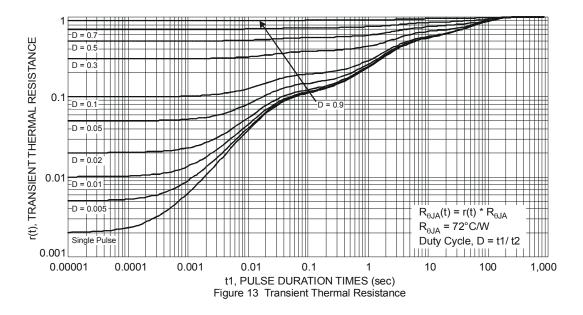






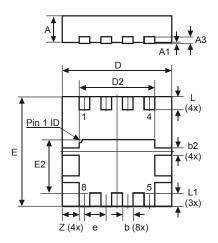
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# **Package Outline Dimensions**

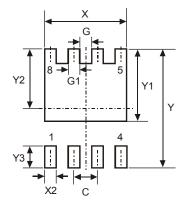
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI3333-8						
Dim	Min	Max	Тур			
D	3.25	3.35	3.30			
Е	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
E2	1.56	1.66	1.61			
Α	0.75	0.85	0.80			
A1	0	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	-	-	0.20			
L	0.35	0.45	0.40			
L1	_	_	0.39			
e	_	_	0.65			
Ζ	-	-	0.515			
All Dimensions in mm						

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	0.650			
G	0.230			
G1	0.420			
Y	3.700			
Y1	2.250			
Y2	1.850			
Y3	0.700			
Х	2.370			
X2	0.420			

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